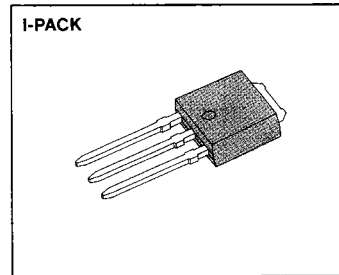


PNP Transistor KSB906 datasheet

LOW FREQUENCY POWER AMPLIFIER

- Low Collector Emitter Saturation Voltage
- Complement to KSD1221



ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	-60	V
Collector Emitter Voltage	V_{CEO}	-60	V
Emitter Base Voltage	V_{EBO}	-7	V
Collector Current	I_C	-3	A
Base Current	I_B	-0.5	A
Collector Dissipation ($T_c = 25^\circ\text{C}$)	P_c	20	W
Collector Dissipation ($T_a = 25^\circ\text{C}$)	P_c	1	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Emitter Breakdown Voltage	BV_{CEO}	$I_C = -50\text{mA}, I_B = 0$	-60			V
Collector Cutoff Current	I_{CBO}	$V_{CB} = -60\text{V}, I_E = 0$			-100	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -7\text{V}, I_C = 0$			-100	μA
DC Current Gain	h_{FE1}	$V_{CE} = -5\text{V}, I_C = -0.5\text{A}$	60		200	
		$h_{FE2} = -5\text{V}, I_C = -3\text{A}$	20			
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -3\text{A}, I_B = -0.3\text{A}$		-1	-1.7	V
Base Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = -5\text{A}, I_C = -0.1\text{A}$		-1	-1.5	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -5\text{V}, I_C = -0.5\text{A}$		9		MHz
Output Capacitance	C_{OB}	$V_{CB} = -10\text{V}, f = 1\text{MHz}$		150		pF
Turn On Time	t_{on}	$-I_{B1} = I_{B2} = 0.2\text{A}$		0.4		μs
Storage Time	t_{stg}	$V_{CC} = -30\text{V}$		1.7		μs
Fall Time	t_f			0.5		μs

h_{FE} CLASSIFICATION

Classification	O	Y
h_{FE}	60 ~ 120	100 ~ 200

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